ABSOLUTE MAXIMUM RATINGS

V _{CC} to GND	0.3V to +4.0V
IN_, EN, EN to GND0.3V	to (V _{CC} + 0.3V)
OUT_+, OUT to GND	0.3V to +4.0V
Short-Circuit Duration (OUT_+, OUT)	Continuous
Continuous Power Dissipation ($T_A = +70^{\circ}C$)	
16-Pin QFN (derate 18.5mW/°C above +70°C)	1481mW
16-Pin TSSOP (derate 9.4mW/°C above +70°C	C)755mW

Storage Temperature Range	65°C to +150°C
Maximum Junction Temperature	+150°C
Operating Temperature Range	
ESD Protection	
Human Body Model, OUT_+, OUT	±8kV
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

 $(V_{CC} = +3.0V \text{ to } +3.6V, R_L = 27\Omega \pm 1\%, EN = \text{high}, \overline{EN} = \text{low}, T_A = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted}.$ Typical values are at V_{CC} = +3.3V, T_A = +25^{\circ}\text{C}.) (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
BLVDS OUTPUTS (OUT_+, OUT_)					
Differential Output Voltage	Vod	Figure 1	250	371	450	mV
Change in Magnitude of V _{OD} Between Complementary Output States	ΔV _{OD}	Figure 1		1	25	mV
Offset Voltage	VOS	Figure 1	1.125	1.29	1.375	V
Change in Magnitude of V _{OS} Between Complementary Output States	ΔV _{OS}	Figure 1		5	25	mV
Output High Voltage	VOH			1.465	1.6	V
Output Low Voltage	Vol		0.90	1.085		V
Differential Output Short-Circuit Current	I _{OSD}	$V_{OD} = 0$			20	mA
Output Short-Circuit Current	IOS	OUT_+ = 0 at IN_ = V _{CC} or OUT = 0 at IN_ = 0			-20	mA
Output High-Impedance Current	I _{OZ}	Disabled, OUT_+ = 0 or V _{CC} , OUT = 0 or V _{CC}	-1		1	μΑ
Power-Off Output Current	IOFF	$V_{CC} = 0$ or open, EN = $\overline{EN} = IN_{-} = 0$, OUT_+ = 0 or 3.6V, OUT = 0 or 3.6V	-1		1	μΑ
Output Capacitance	Cout	Capacitance from OUT_+ or OUT to GND		4.3		pF
INPUTS (IN_, EN, EN)			1			
High-Level Input Voltage	VIH		2.0		Vcc	V
Low-Level Input Voltage	VIL		GND		0.8	V
Input Current	l _{IN}	IN_, EN, $\overline{EN} = 0$ or V _{CC}	-15		15	μA
SUPPLY CURRENT						
Supply Current	Icc	$R_L = 27\Omega$, $IN_{-} = V_{CC}$ or 0 for all channels		58	70	mA
Disabled Supply Current	ICCZ	Disabled		3.2	5	mA

AC ELECTRICAL CHARACTERISTICS

 $(V_{CC} = +3.0V \text{ to } +3.6V, R_L = 27\Omega \pm 1\%, C_L = 15pF, EN = high, \overline{EN} = low, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, unless otherwise noted. Typical values are at V_{CC} = +3.3V, T_A = +25^{\circ}C.)$ (Notes 3, 4, 5)

PARAMETER	SYMBOL	CON	DITIONS	MIN	ТҮР	MAX	UNITS
Differential Propagation Delay High to Low	^t PHLD	Figures 2 and 3		1.0	1.98	3.0	ns
Differential Propagation Delay Low to High	^t PLHD	Figures 2 and 3		1.0	1.92	3.0	ns
Differential Pulse Skew (Note 6)	tskD1	Figures 2 and 3				300	ps
Differential Channel-to-Channel Skew (Note 7)	tSKD2	Figures 2 and 3				450	ps
Differential Part-to-Part Skew (Note 8)	tsкdз	Figures 2 and 3				1.2	ns
Differential Part-to-Part Skew (Note 9)	tSKD4	Figures 2 and 3				2.0	ns
Rise Time	+	Figures 2 and 3	MAX9129EGE	0.60	1.19	1.55	20
nise nine	tτlh	Figures 2 and 3	MAX9129EUE	0.60	1.09	1.40	ns
Fall Time	+	Figures 2 and 2	MAX9129EGE	0.60	1.12	1.55	20
	tthl	Figures 2 and 3	MAX9129EUE	0.60	1.02	1.40	ns
Disable Time High to Z	t _{PHZ}	Figures 4 and 5				8	ns
Disable Time Low to Z	t _{PLZ}	Figures 4 and 5				8	ns
Enable Time Z to High	tpzh	Figures 4 and 5				10	ns
Enable Time Z to Low	t _{PZL}	Figures 4 and 5				10	ns
Maximum Operating Frequency (Note 10)	f _{MAX}	Figure 2		100			MHz

Note 1: Maximum and minimum limits over temperature are guaranteed by design and characterization. Devices are 100% tested at $T_A = +25^{\circ}C$.

Note 2: Current into the device is defined as positive, and current out of the device is defined as negative. All voltages are referenced to ground except V_{OD} and ΔV_{OD} .

Note 3: AC parameters are guaranteed by design and characterization.

Note 4: C_L includes probe and jig capacitance.

Note 5: Signal generator conditions: $V_{OL} = 0$, $V_{OH} = V_{CC}$, f = 100MHz, 50% duty cycle, $R_O = 50\Omega$, $t_R = t_F = 1$ ns (10% to 90%).

Note 6: t_{SKD1} is the magnitude difference of differential propagation delays. t_{SKD1} = | t_{PHLD} - t_{PLHD} |.

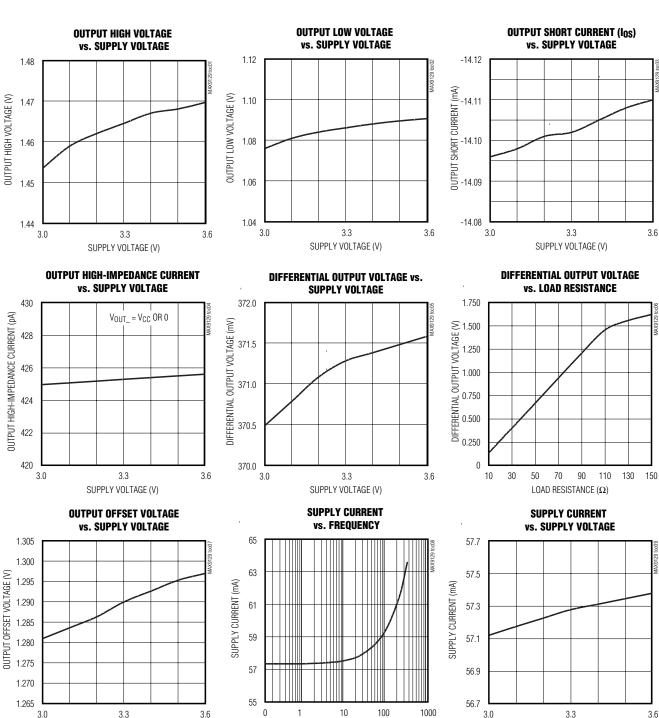
Note 7: t_{SKD2} is the magnitude difference of t_{PHLD} or t_{PLHD} of one channel to the t_{PHLD} or t_{PLHD} of another channel on the same device.

Note 8: t_{SKD3} is the magnitude difference of any differential propagation delays between devices at the same V_{CC} and within 5°C of each other.

Note 9: t_{SKD4} is the magnitude difference of any differential propagation delays between devices operating over the rated supply and temperature ranges.

Note 10: Signal generator conditions: $V_{OL} = 0$, $V_{OH} = V_{CC}$, f = 100MHz, 50% duty cycle, $R_O = 50\Omega$, $t_R = t_F = 1$ ns (10% to 90%). MAX9129 output criteria: duty cycle = 45% to 55%, $V_{OD} \ge 250$ mV, all channels switching. **MAX9129**





FREQUENCY (MHz)

Typical Operating Characteristics

SUPPLY VOLTAGE (V)

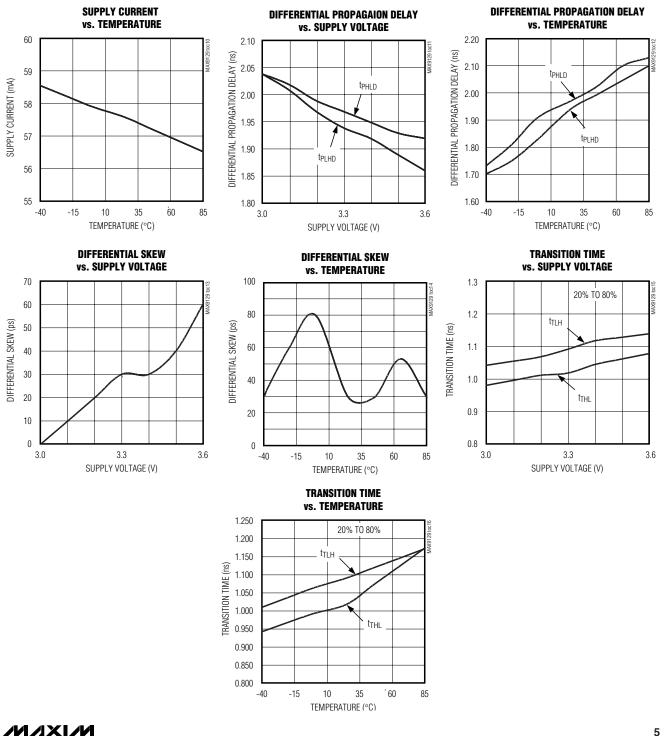
(MAX9129EUE (TSSOP package), $V_{CC} = +3.3V$, $R_L = 27\Omega$, $C_L = 15pF$, $T_A = +25^{\circ}C$, unless otherwise noted.) (Note 5)

4

SUPPLY VOLTAGE (V)

Typical Operating Characteristics (continued)

(MAX9129EUE (TSSOP package), V_{CC} = +3.3V, R_L = 27Ω, C_L = 15pF, T_A = +25°C, unless otherwise noted.) (Note 5)



MAX9129

MAX9129

			Pin Description
Р	IN	NAME	EUNCTION
QFN	TSSOP	NAME	FUNCTION
15	1	EN	LVTTL/LVCMOS Enable Input. The driver is disabled when EN is low. EN is internally pulled down. When EN = high and $\overline{\text{EN}}$ = low or open, the outputs are active. For other combinations of EN and $\overline{\text{EN}}$, the outputs are disabled and are high impedance.
1, 4, 5, 16	2, 3, 6, 7	IN_	LVTTL/LVCMOS Driver Inputs
2	4	V _{CC}	Power-Supply Input. Bypass V _{CC} to GND with 0.1 μ F and 0.001 μ F ceramic capacitors.
3	5	GND	Ground
6	8	ĒN	LVTTL/LVCMOS Enable Input. The driver is disabled when $\overline{\text{EN}}$ is high. $\overline{\text{EN}}$ is internally pulled down.
7, 10, 11, 14	9, 12, 13, 16	OUT	Inverting BLVDS Driver Outputs
8, 9, 12, 13	10, 11, 14, 15	OUT_+	Noninverting BLVDS Driver Outputs

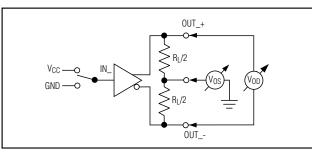


Figure 1. Driver V_{OD} and V_{OS} Test Circuit

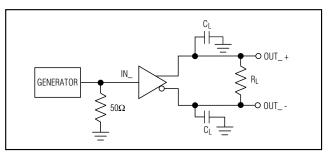


Figure 2. Driver Propagation Delay and Transition Time Test Circuit

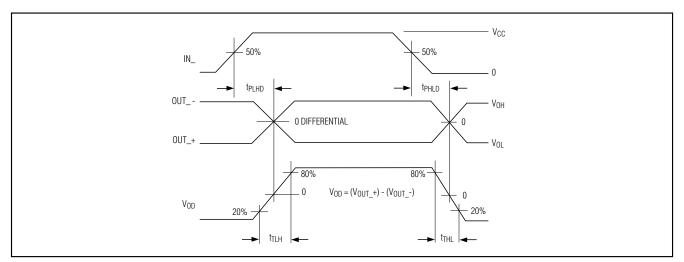


Figure 3. Driver Propagation Delay and Transition Time Waveforms

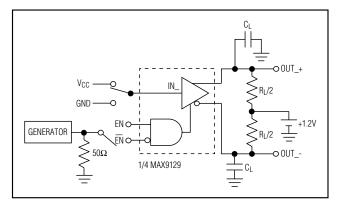


Figure 4. Driver High-Impedance Delay Test Circuit

Table 1. Input/Output Function Table

ENAB	LES	INPUTS	OUT	PUTS
EN <u>EN</u>		IN_	OUT_+	OUT
		L	L	Н
Н	L or open	Н	Н	L
All other com EN an		Х	Z	Z

MAX9129

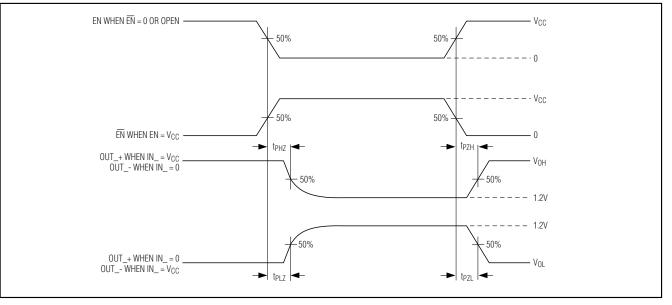


Figure 5. Driver High-Impedance Delay Waveform

Detailed Description

The MAX9129 is a 200Mbps quad differential BLVDS driver designed for multipoint, heavily loaded backplane applications. This device accepts LVTTL/LVCMOS input levels and translates them to output levels of 250mV to 450mV into a 27 Ω load. The flow-through pinout simplifies board layout and reduces the potential for crosstalk between single-ended inputs and differential outputs. Transition times are designed to reduce reflections, yet enable high data rates. The MAX9129 can be used in conjunction with standard quad LVDS receivers, such



as the MAX9121, to implement full-duplex multipoint buses more efficiently than with transceivers.

Effect of Capacitive Loading

The characteristic impedance of a differential PC board trace is uniformly reduced when equal capacitive loads are attached at equal intervals (provided the transition time of the signal being driven on the trace is longer than the delay between loads). This kind of loading is typical of multipoint buses where cards are attached at 1 in or 0.8 in intervals along the length of a backplane.

The reduction in characteristic impedance is approximated by the following formula:

 $ZDIFF-loaded = ZDIFF-unloaded \times SQRT [C_0 / (C_0 + N \times C_L / L)]$

where:

ZDIFF-unloaded = unloaded differential characteristic impedance

 C_0 = unloaded trace capacitance (pF/unit length)

 C_L = value of each capacitive load (pF)

N = number of capacitive loads

L = trace length

For example, if $C_0 = 2.5 pF/in$, $C_L = 10 pF$, N = 18, L = 18in, and $Z_{DIFF-unloaded} = 120 \Omega$, the loaded differential impedance is:

 $Z_{\text{DIFF-loaded}} = 120\Omega \times \text{SQRT} [2.5\text{pF} / (2.5\text{pF} + 18 \times 10\text{pF}/18\text{in})]$

ZDIFF-loaded = 54Ω

In this example, capacitive loading reduces the characteristic impedance from 120Ω to 54Ω . The load seen by a driver located on a card in the middle of the bus is 27Ω because the driver sees two 54Ω loads in parallel. A typical LVDS driver (rated for a 100Ω load) would not develop a large enough differential signal to be reliably detected by an LVDS receiver. Maxim's BLVDS driver is designed and specified to drive a 27Ω load to differential voltage levels of 250mV to 450mV (which are standard LVDS driver levels). A standard LVDS receiver is able to detect this level of differential signal.

Short extensions off the bus, called stubs, contribute to capacitive loading. Keep stubs less than 1in for a good balance between ease of component placement and good signal integrity.

The MAX9129 is a current source driver and drives larger differential signal levels into loads higher than 27Ω and smaller levels into loads less than 27Ω (see typical operating curves). To keep loading from reducing bus impedance below the rated 27Ω load, PC board traces can be designed for higher unloaded characteristic impedance.

Effect of Transition Time

For transition times (measured from 0% to 100%) shorter than the delay between capacitive loads, the loads are seen as low-impedance discontinuities from which the driven signal is reflected. Reflections add and subtract from the signal being driven and cause decreased noise margin and jitter. The MAX9129 is designed for a minimum transition time of 1ns (rated 0.6ns from 20% to 80%, or about 1ns 0% to 100%) to reduce reflections while being fast enough for high-speed backplane data transmission.

Power-On Reset

The power-on reset voltage of the MAX9129 is typically 2.25V. When the supply falls below this voltage, the device is disabled and the outputs are in high impedance.

Applications Information

Power-Supply Bypassing

Bypass V_{CC} with high-frequency, surface-mount ceramic 0.1μ F and 0.001μ F capacitors in parallel as close to the device as possible, with the smaller valued capacitor closest to V_{CC}.

Termination

In the example above, the loaded differential impedance of the bus is reduced to 54Ω . Since it can be driven from any card position, the bus must be terminated at each end. A parallel termination of 54Ω at each end of the bus placed across the traces that make up the differential pair provides a proper termination. The total load seen by the driver is 27Ω .

The MAX9129 drives higher differential signal levels into lighter loads. A multidrop bus with the driver at one end and receivers connected at regular intervals along the bus has a lowered impedance due to capacitive loading. Assuming the same impedance calculated in the multidrop example above (54 Ω), the multidrop bus can be terminated with a single, parallel-connected 54 Ω resistor at the far end from the driver. Only a single resistor is required because the driver sees one 54 Ω differential trace. The signal swing is larger with a 54 Ω load.

In general, parallel terminate each end of the bus with a resistor matching the differential impedance of the bus (taking into account any reduced impedance due to loading).

Board Layout

M/XI/M

A four-layer PC board that provides separate power, ground, input, and output signals is recommended. Keep the LVTTL/LVCMOS and BLVDS signals separated to prevent coupling as shown in the suggested layout for the QFN package (not drawn to scale) (Figure 6).

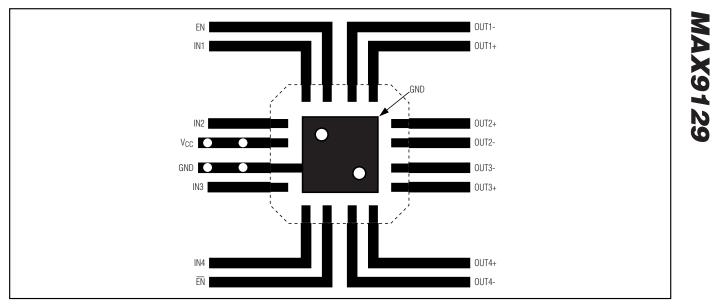
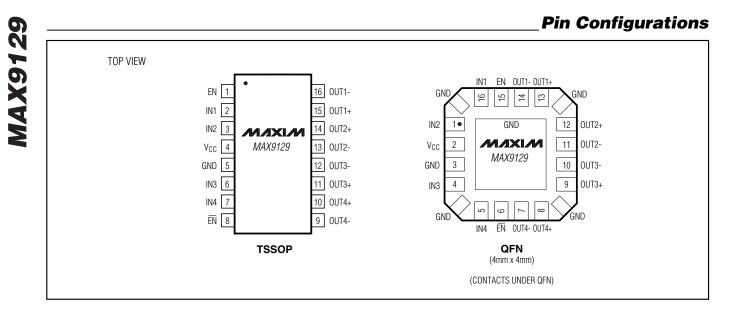


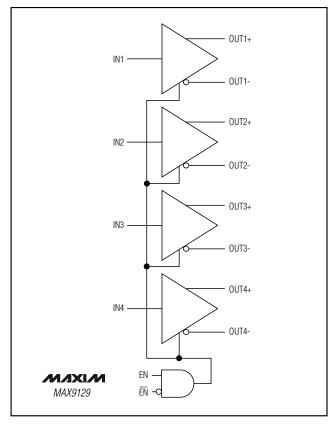
Figure 6. Suggested Layout for QFN Package

Chip Information

TRANSISTOR COUNT: 948 PROCESS: CMOS

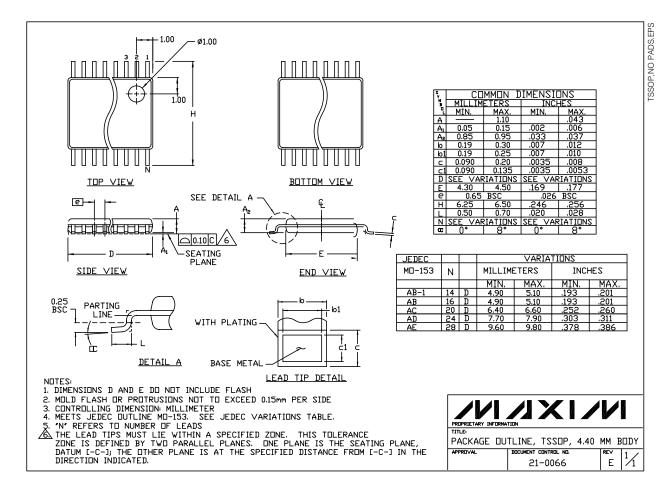


Functional Diagram



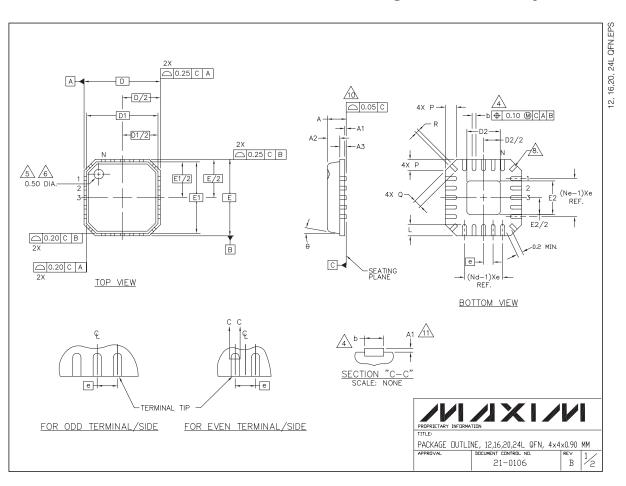
M/XI/M

Package Information



MAX9129

MAX9129



Package Information (continued)

Package Information (continued)

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12. WEETS * PITCI MIN. N Ne L L 0.50 b 0.28 Q 0.30 D2 SEE EXPO SYMBOLS EXPOSED F	JEDEC MC + VARIAT NOM. 0.80 BSC 3 0.60 0.33 0.40 0.40 SED PAD VARI SED PAD VARI PAD A 1.5 SED B 1.5	0220. ION A MAX. 0.75 0.40 0.55 0.40 0.40 0.55 0.40 0.40 0.55 0.40 0.40 0.55 0.40 0.40 0.55 0.40	Norre 0 3 N 3 N 3 N 4 b Q D2 E2 MAX 2.25 1.85	MIN. 0.50 0.23 0.30 SEE EXPOS SEE EXPOS SEE EXPOS 1.55 1	NOM. 0.65 BSC 16 4 4 0.60 0.28 0.40 ED PAD EO MAX .10 2.25 .70 1.85	0.75 0.35 0.65 IATION: A, E IATION: A, C	Ι Ι 3 Nd 3 Nd 3 Ne 4 b Q D2 E2	MIN. 0.50 0.18 0.30 SEE EXPOS	NOM. 0.50 BSC 5 5 0.60 0.23 0.40 SED PAD VAR	0.75 0.30 0.65 IATION: A, B	° _{те}	Nd Nd Ne L D2 E2	MIN. (0.30 0.18 0.00 SEE EXPOSI	NOM. 0.50 BSC 24 6 0.40 0.23 0.20 ED PAD VA ED PAD VA	0.5 0.3/ 0.4 ARIATION	X. "•, 3 3 3 5 0 4 5 :A :A
12. WEETS PITCI MIN. N Ne L 0.50 b 0.28 Q 0.30 D2SEE EXPO SYMBOLS EXPOSED F VARIATION EXAMPLE: 1	JEDEC MC H VARIAT NOM. 0.80 BSC 12 3 0.60 0.33 0.40 0.80 PAD VARI SED PAD VARI MI PAD A 1.5 NS NS B NE CAN CA	D220. 10N A MAX. 0.75 0.40 0.65 ATION: A, B D2 N NOM 25 2.10 35 1.70 NL VARIA	Nor _E 0 3 Nd 3 Nd 3 Nd 3 Nd 3 Nd 2 L 4 b Q D2 E2 MAX 2.25 1.85 TION "E	MIN. 0.50 0.23 0.30 SEE EXPOS SEE EXPOS MIN N 1.95 2 1.55 1 BB" FOR	NOM. 0.65 BSC 16 4 4 0.60 0.28 0.40 0.40 0.40 SED PAD VAR SED PAD VAR E2 IOM MAX .10 2.25 .70 1.85 16 TERMIN	0.75 0.35 0.65 IATION: A, E NOTE	τε τε (Ξ) 3 3 Nd 3 Nd 4 b Q D2 E2	MIN. 0.50 0.18 0.30 SEE EXPOS	NOM. 0.50 BSC 5 5 0.60 0.23 0.40 SED PAD VAR	0.75 0.30 0.65 IATION: A, B		Nd Nd Ne L D2 E2	MIN. [0.30 0.18 0.00 SEE EXPOSI	NOM. 0.50 BSC 24 6 0.40 0.23 0.20 ED PAD VA ED PAD VA	0.5 0.3/ 0.4 ARIATION	X. "•, 3 3 3 5 0 4 5 :A :A
12. WEETS PITCI N N N L 0.50 b 0.28 0.30 D2SEE EXPO SYMBOLS EXPOSED F VARIATION EXAMPLE:	JEDEC MC + VARIAT NOM. 0.80 BSC 3 0.60 0.33 0.40 0.40 SED PAD VARI SED PAD VARI PAD A 1.5 SED B 1.5	0220. 10N A MAX. 0.75 0.40 0.55 1.70	% %	MIN. 0.50 0.23 0.30 SEE EXPOS SEE EXPOS MIN N 1.95 2 1.55 1 B [®] FOR AL EXPO	NOM. 0.65 BSC 16 4 0.60 0.28 0.40 VAR EED PAD VAR EED PAD VAR E2 100M MAX 110 2.25 .70 1.85 16 TERMIH SED PAD	0.75 0.35 0.65 IATION: A, E NOTE	τε σ Image: Constraint of the second	MIN. 0.50 0.18 0.30 SEE EXPOS	NOM. 0.50 BSC 5 5 0.60 0.23 0.40 SED PAD VAR	0.75 0.30 0.65 IATION: A, B IATION: A, B	° _T	B N N N D C C N D C C C N N D C C C N N D C C C N N D C C C N N D C C C N N D C C C C C C C C C C C C C	0.30 0.18 0.00 SEE EXPOSI SEE EXPOSI	NOM. 0.50 BSC 24 6 6 0.40 0.23 0.20 ED PAD VA ED PAD VA	0.5 0.30 0.4 ARIATION	X. 3 3 5 0 4 5 :A :A
12. WEETS ************************************	JEDEC MC H VARIAT NOM. 0.80 BSC 12 3 0.60 0.33 0.40 0.80 PSC SED PAD VARI MI PAD A 1.5 MI VAR B 1.5 NS B 1.5 WE CAN CA MITH 1.70×	D220.	№ №	MIN. 0.50 0.23 0.30 SEE EXPOS SEE EXPOS MIN N 1.95 2 1.55 1 BB" FOR AL EXPO TION IS F	NOM. 0.65 BSC 16 4 0.60 0.28 0.40 0.28 0.40 0.40 0.40 0.28 0.40 0.28 0.40 0.28 0.40 0.28 0.40 0.28 0.40 0.28 1.15 1	O.75 O.35 O.65 IATION: A, E IATION: A, E NOTE	• • • • • • • • • • • • • • • • • • •	MIN. 0.50 0.18 0.30 SEE EXPOS	NOM. 0.50 BSC 5 5 0.60 0.23 0.40 SED PAD VAR	0.75 0.30 0.65 IATION: A, B IATION: A, B	°TE	B N N N D C C N D C C C N N D C C C N N D C C C N N D C C C N N D C C C N N D C C C C C C C C C C C C C	MIN. [0.30 0.18 0.00 SEE EXPOSI SEE EXPOSI ATION INE, 12,16	NOM. 0.50 BSC 24 6 6 0.40 0.23 0.20 ED PAD VA ED PAD VA	0.5 0.30 0.4 ARIATION	X. 3 3 5 0 4 5 :A :A

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